

Abstract of the Disclosure

An interconnection is formed on a semiconductor substrate having a semiconductor element formed thereon. Next, a passivation
5 film is formed on the semiconductor substrate including the interconnection. Further, a polyimide film, which is served as a buffer coating film, is formed on the passivation film. Further, the polyimide film is patterned. Next, the passivation film is subject
10 to etching while the patterned polyimide film is taken as a mask. Next, a hardened layer, which is formed on the surface of the polyimide film as a result of etching, is removed through ashing process. Next, the semiconductor substrate after ashing process is cured so as to transform the polyimide film into imide.